Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series CT" triac will commutate the full RMS current at the maximum rated junction temperature ($T_j = 150~{\rm ^{\circ}C}$) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction operating temperature capability
- · High voltage capability
- Less sensitive gate for high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	100	A
T _j	junction temperature		-	-	150	°C
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 125 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	12	А





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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static char	acteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 6$		2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 6}}$		2	-	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 6$		2	-	35	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—71
2	T2	main terminal 2	705	sym051
3	G	gate		Symoon
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BTA312-600CT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 125 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	12	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	100	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	110	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	50	A ² s
dI _T /dt	rate of rise of on-state current	I _G = 70 mA	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P_GM	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

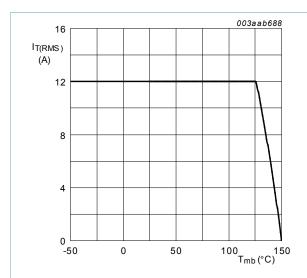
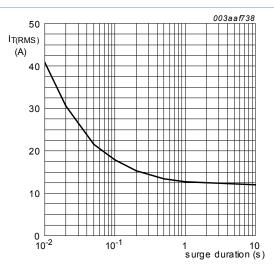


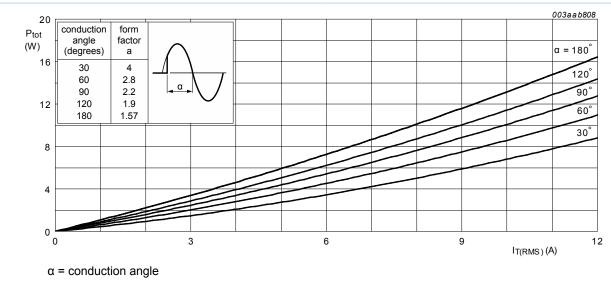
Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 125 \,^{\circ}\text{C}$

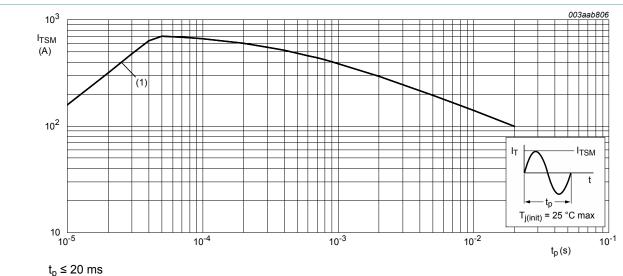
Fig. 2. RMS on-state current as a function of surge duration; maximum values

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a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Total power dissipation as a function of RMS on-state current; maximum values Fig. 3.



(1) dI_T/dt limit

Non-repetitive peak on-state current as a function of pulse duration; maximum values Fig. 4.

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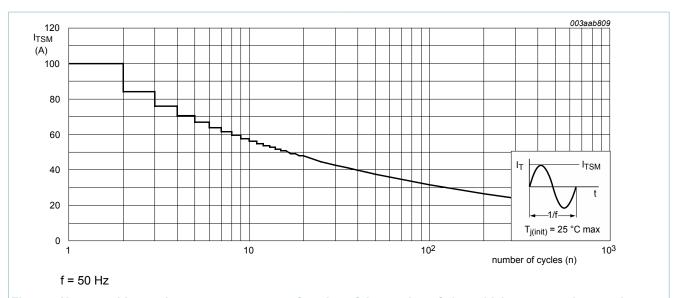


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

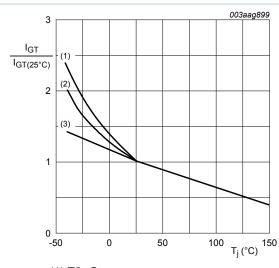
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)} thermal resistance		full cycle	-	-	1.5	K/W
	from junction to mounting base	half cycle	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
lgт	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 6$	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 6$	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 6$	2	-	35	mA
l _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	50	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 8</u>	-	-	35	mA
V _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 9</u>	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 10	-	0.8	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 150 °C; Fig. 10	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 150 °C	-	0.4	2	mA
Dynamic o	haracteristics		,			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	300	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	8	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 10 V/ μ s; gate open circuit	13	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 1 V/µs; gate open circuit	20	-	-	A/ms

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- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 6. Normalized gate trigger current as a function of junction temperature

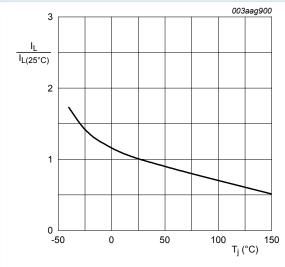


Fig. 7. Normalized latching current as a function of junction temperature

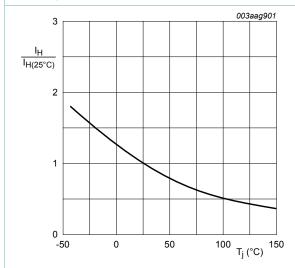
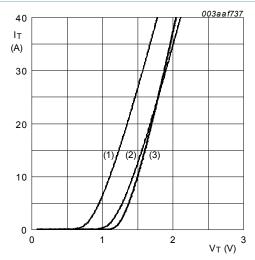


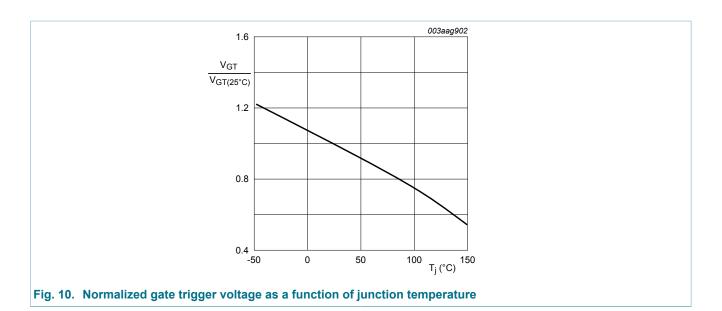
Fig. 8. Normalized holding current as a function of junction temperature



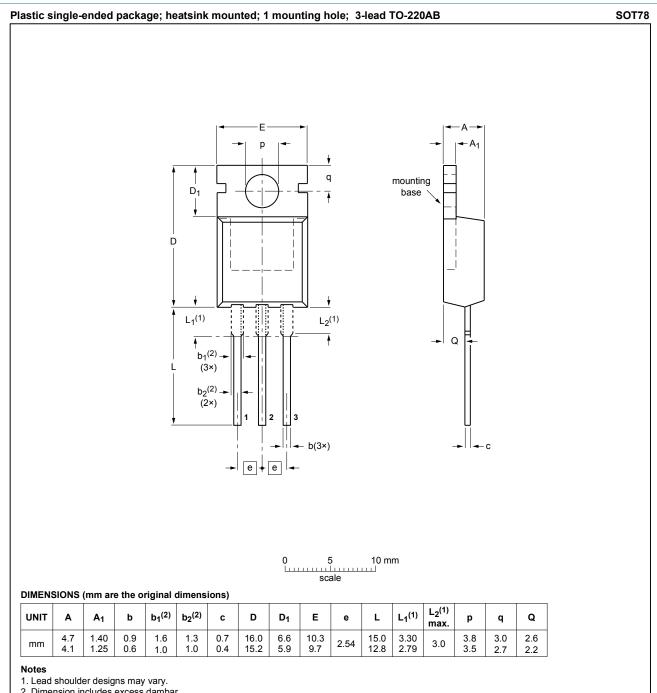
- $V_0 = 1.164 \text{ V}; R_s = 0.027 \Omega$
- (1) T_i = 150 °C; typical values
- (2) T_i = 150 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 9. On-state current as a function of on-state voltage

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10. Package outline



2. Dimension includes excess dambar.

OUTLINE	OUTLINE REFERENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig. 11. Package outline TO-220AB (SOT78)

BTA312-600CT

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